

# **General Purpose Transistors**

#### **NPN Silicon**

# BC846, BC847, BC848

These transistors are designed for general purpose amplifier applications. They are housed in the SC-70/SOT-323 which is designed for low power surface mount applications.

#### **Features**

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

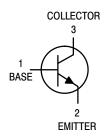
Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC846 BC847 BC848	V <sub>CEO</sub>	65 45 30	٧
Collector-Base Voltage BC846 BC847 BC848	V <sub>CBO</sub>	80 50 30	V
Emitter-Base Voltage BC846 BC847 BC848	V <sub>EBO</sub>	6.0 6.0 5.0	V
Collector Current - Continuous	I <sub>C</sub>	100	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T <sub>A</sub> = 25 °C	$P_{D}$	200	mW
Thermal Resistance, Junction-to-Ambient	$R_{\thetaJA}$	620	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

1.  $FR-5 = 1.0 \times 0.75 \times 0.062$  in.





SC-70/SOT-323 CASE 419 STYLE 3

#### **MARKING DIAGRAM**



XX = Specific Device Code M = Month Code

= Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

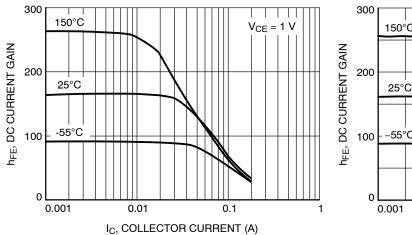
See detailed ordering, marking and shipping information on page 12 of this data sheet.

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25$ $^{\circ}C$ unless otherwise noted)

	Symbol	Min	Тур	Max	Unit		
OFF CHARACTERISTICS			•	•		•	
Collector - Emitter Breakdown (I <sub>C</sub> = 10 mA)	Voltage	BC846 Series BC847 Series BC848 Series	V <sub>(BR)CEO</sub>	65 45 30	- - -	- - -	V
Collector - Emitter Breakdown ( $I_C = 10 \mu A, V_{EB} = 0$ )	Voltage	BC846 Series BC847 Series BC848 Series	V <sub>(BR)</sub> CES	80 50 30	- - -	- - -	V
Collector - Base Breakdown Vo $(I_C = 10 \mu A)$	ltage	BC846 Series BC847 Series BC848 Series	V <sub>(BR)</sub> CBO	80 50 30	- - -	- - -	V
Emitter - Base Breakdown Volta ( $I_E = 1.0 \mu A$ )	age	BC846 Series BC847 Series BC848 Series	V <sub>(BR)EBO</sub>	6.0 6.0 5.0	- - -	- - -	V
Collector Cutoff Current	(V <sub>CB</sub> = 30 V) (V <sub>CB</sub> = 30 V, T <sub>A</sub> = 150°C)		I <sub>CBO</sub>	- -	- -	15 5.0	nA μA
ON CHARACTERISTICS							
DC Current Gain ( $I_C = 10 \mu A, V_{CE} = 5.0 V$ )		846A, BC847A, BC848A 846B, BC847B, BC848B BC847C, BC848C	h <sub>FE</sub>	- - -	90 150 270	- - -	-
$(I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC846A, BC847A, BC848A BC8	A 346B, BC847B, BC848B BC847C, BC848C		110 200 420	180 290 520	220 450 800	
Collector - Emitter Saturation V	oltage ( $I_C$ = 10 mA, $I_B$ = 0.5 ( $I_C$ = 100 mA, $I_B$ = 5.0 m	*	V <sub>CE(sat)</sub>	- -	- -	0.25 0.6	V
Base-Emitter Saturation Volta	ge ( $I_C$ = 10 mA, $I_B$ = 0.5 mA ( $I_C$ = 100 mA, $I_B$ = 5.0 m		V <sub>BE(sat)</sub>	- -	0.7 0.9	- -	V
Base-Emitter Voltage ( $I_C = 2.0$ ) ( $I_C = 10$ )	0 mA, V <sub>CE</sub> = 5.0 V) 0 mA, V <sub>CE</sub> = 5.0 V)		V <sub>BE(on)</sub>	580 -	660 -	700 770	mV
SMALL-SIGNAL CHARACTE	RISTICS						
Current - Gain $-$ Bandwidth Pro (I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 5.0 Vdc, f			f <sub>T</sub>	100	_	_	MHz
Output Capacitance (V <sub>CB</sub> = 10	V, f = 1.0 MHz)		C <sub>obo</sub>	-	-	4.5	pF
Noise Figure (I <sub>C</sub> = 0.2 mA, V <sub>CI</sub>	$= 5.0 \text{ Vdc}, R_S = 2.0 \text{ k}Ω, f = 1.0 \text{ k}Ω$	= 1.0 kHz, BW = 200 Hz)	NF	_	_	10	dB
· · · · · · · · · · · · · · · · · · ·							

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### BC846A, BC847A, BC848A



V<sub>CE</sub> = 5 V 150°C -55°C 0.01 0.1 I<sub>C</sub>, COLLECTOR CURRENT (A)

Figure 1. DC Current Gain vs. Collector Current

Figure 2. DC Current Gain vs. Collector Current

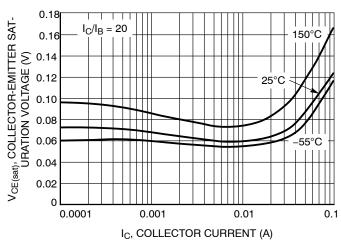


Figure 3. Collector Emitter Saturation Voltage vs. Collector Current

1.2

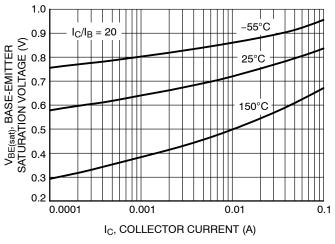
1.1

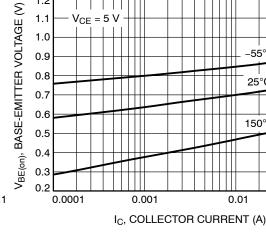
1.0

0.9

0.8

0.7





V<sub>CE</sub> = 5 V

Figure 4. Base Emitter Saturation Voltage vs. **Collector Current** 

Figure 5. Base Emitter Voltage vs. Collector Current

-55°C

25°C

150°C

0.1

#### BC846A, BC847A, BC848A

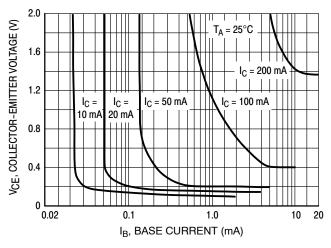
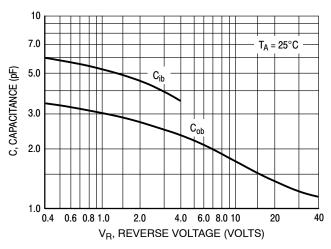


Figure 6. Collector Saturation Region

Figure 7. Base-Emitter Temperature Coefficient



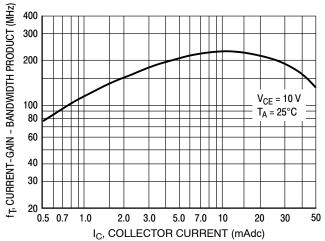
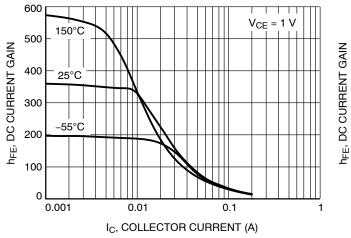


Figure 8. Capacitances

Figure 9. Current-Gain - Bandwidth Product

#### **BC846B**



600 150°C 400 25°C 25°C 200 25°C 100 0 0.001 0.01 0.1 1 I<sub>C</sub>, COLLECTOR CURRENT (A)

Figure 10. DC Current Gain vs. Collector Current

Figure 11. DC Current Gain vs. Collector Current

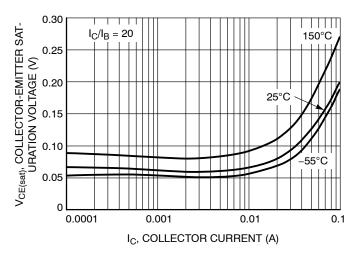
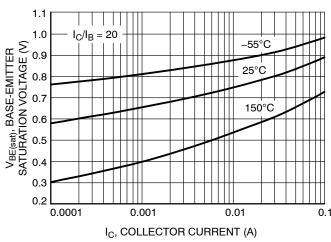


Figure 12. Collector Emitter Saturation Voltage vs. Collector Current



I<sub>C</sub>, COLLECTOR CURRENT (A)

Figure 13. Base Emitter Saturation Voltage vs.

Collector Current

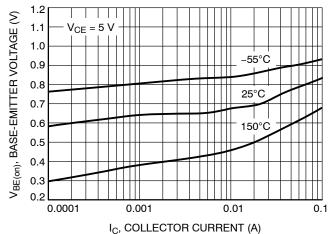
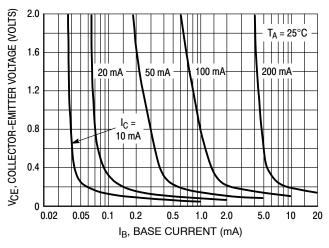


Figure 14. Base Emitter Voltage vs. Collector Current

#### **BC846B**



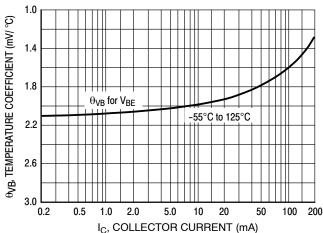


Figure 15. Collector Saturation Region

Figure 16. Base-Emitter Temperature Coefficient

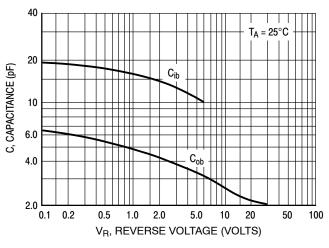


Figure 17. Capacitance

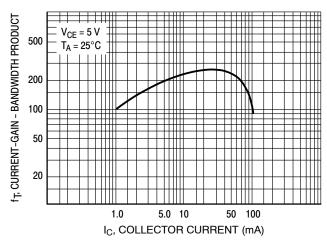
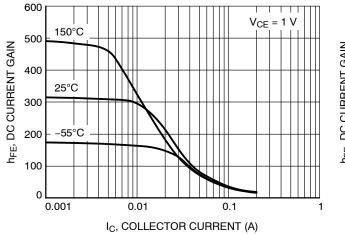


Figure 18. Current-Gain - Bandwidth Product

#### BC847B, BC848B



600  $V_{CE} = 5 V$ 150°C 500 hFE, DC CURRENT GAIN 400 25°C 300 200 -55°C 100 0 0.001 0.01 0.1 IC, COLLECTOR CURRENT (A)

Figure 19. DC Current Gain vs. Collector Current

Figure 20. DC Current Gain vs. Collector Current

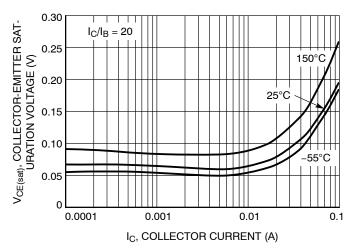


Figure 21. Collector Emitter Saturation Voltage vs. Collector Current

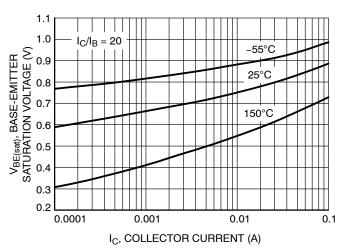


Figure 22. Base Emitter Saturation Voltage vs. Collector Current

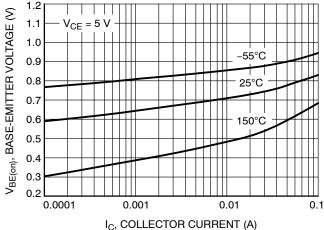


Figure 23. Base Emitter Voltage vs. Collector Current

#### BC847B, BC848B

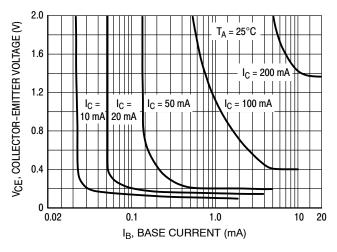


Figure 24. Collector Saturation Region

Figure 25. Base-Emitter Temperature Coefficient

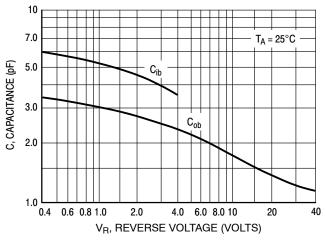


Figure 26. Capacitances

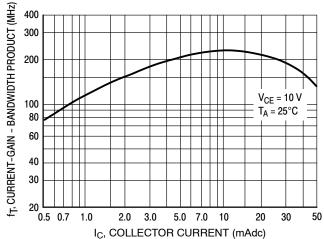
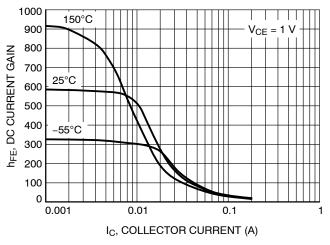


Figure 27. Current-Gain - Bandwidth Product

#### BC847C, BC848C



1000 900 150°C 800 hFE, DC CURRENT GAIN 700 600 25°C 500 400 -55°C 300 200 100 0.001 0.1 I<sub>C</sub>, COLLECTOR CURRENT (A)

Figure 28. DC Current Gain vs. Collector Current

Figure 29. DC Current Gain vs. Collector Current

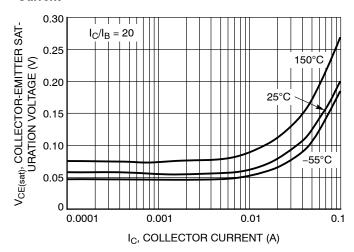


Figure 30. Collector Emitter Saturation Voltage vs. Collector Current

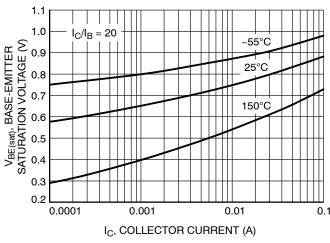


Figure 31. Base Emitter Saturation Voltage vs. Collector Current

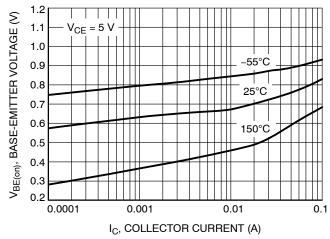
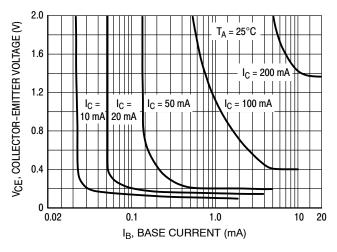


Figure 32. Base Emitter Voltage vs. Collector Current

#### BC847C, BC848C

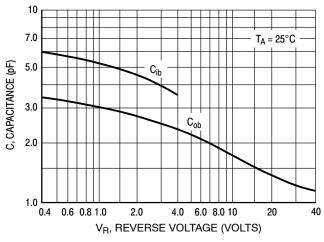
400



1.0 θ√B, TEMPERATURE COEFFICIENT (mV/°C) 1.2 1.6 2.0 2.4 2.8 0.2 1.0 10 100 I<sub>C</sub>, COLLECTOR CURRENT (mA)

Figure 33. Collector Saturation Region

Figure 34. Base-Emitter Temperature Coefficient



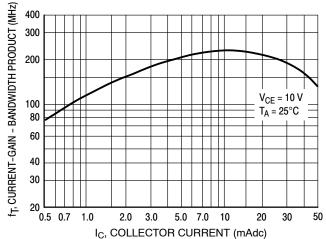


Figure 35. Capacitances

Figure 36. Current-Gain - Bandwidth Product

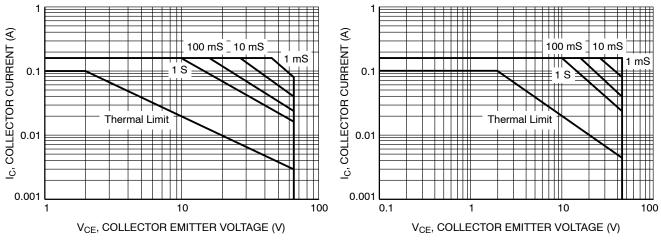


Figure 37. Safe Operating Area for BC846A, BC846B

Figure 38. Safe Operating Area for BC847A, BC847B, BC847C

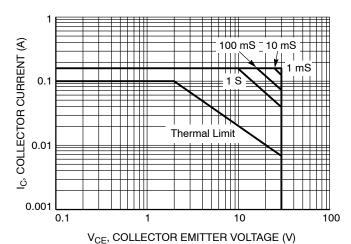


Figure 39. Safe Operating Area for BC848A, BC848B, BC848C

#### **DEVICE ORDERING AND SPECIFIC MARKING INFORMATION**

Device	Specific Marking Code	Package	Shipping <sup>†</sup>	
BC846BWT1G	1B	SC-70 (SOT-323) (Pb-Free)	3,000 / Tape & Reel	
SBC846BWT1G*	IB			
BC847AWT1G	45		0.000 /Table 9 Deal	
SBC847AWT1G*	1E		3,000 / Tape & Reel	
BC847BWT1G	45		3,000 / Tape & Reel	
SBC847BWT1G*	1F			
BC847CWT1G	40		3,000 / Tape & Reel	
SBC847CWT1G*	- 1G			
BC847CWT3G	40		10,000 / Tape & Reel	
SBC847CWT3G*	- 1G			
BC848BWT1G	417			
NSVBC848BWT1G*	1K		3,000 / Tape & Reel	
BC848CWT1G	1L			

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified

and PPAP Capable.







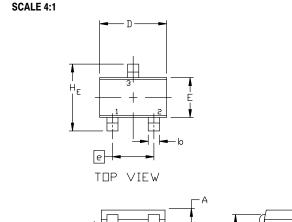
SC-70 (SOT-323) CASE 419 ISSUE R

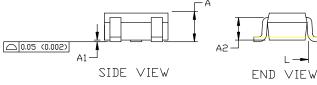
**DATE 11 OCT 2022** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF		0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BS	C
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095





# GENERIC MARKING DIAGRAM

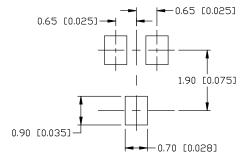


XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	<ol><li>CATHODE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>COLLECTOR</li></ol>	3. DRAIN	<ol><li>CATHODE-ANODE</li></ol>	3. ANODE-CATHODE	<ol><li>CATHODE</li></ol>

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DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1	

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**Authorized Distributor** 

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BC846AWT1 BC846AWT1G BC846BWT1 BC846BWT1G BC847AWT1 BC847AWT1G BC847BWT1

BC847BWT1G BC847CWT1 BC847CWT1G BC848AWT1 BC848AWT1G BC848BWT1 BC848BWT1G

BC848CWT1 BC848CWT1G SBC847BWT1G SBC846BWT1G SBC847AWT1G SBC847CWT1G BC847CWT3G

SBC847CWT3G NSVBC848BWT1G